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FIG. 1

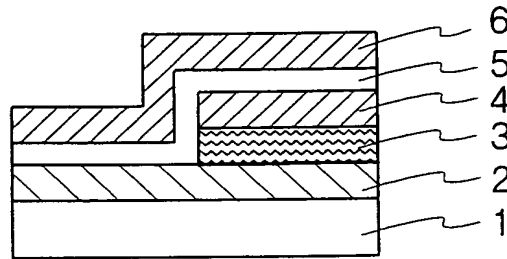


FIG. 2 A

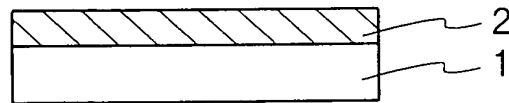


FIG. 2 B

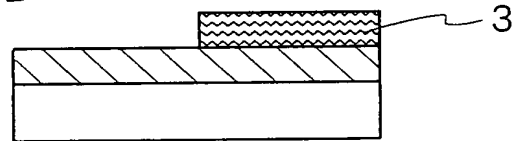


FIG. 2 C

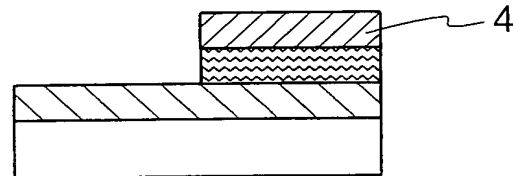
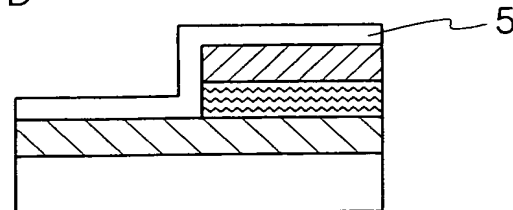


FIG. 2 D



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FIG. 3A

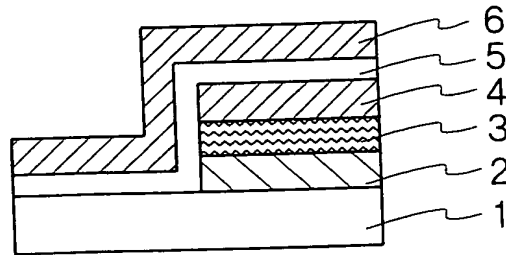


FIG. 3B

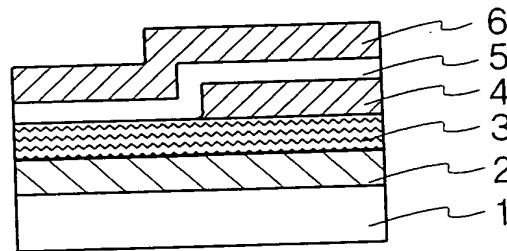
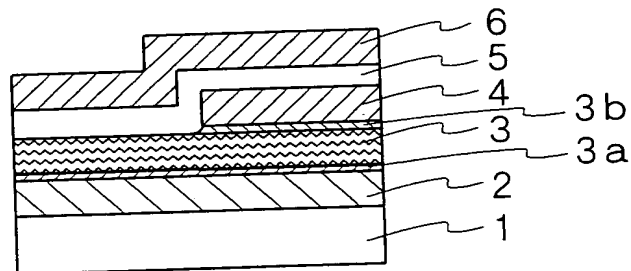


FIG. 4



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FIG. 5A

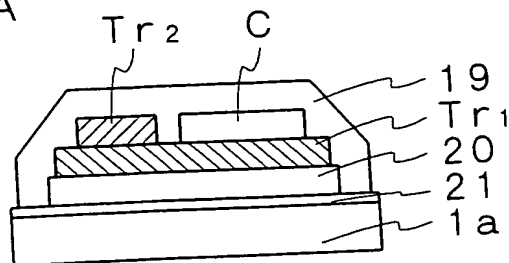


FIG. 5B

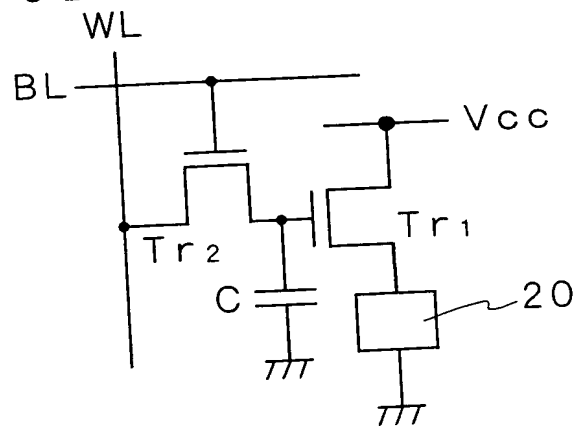


FIG. 5C

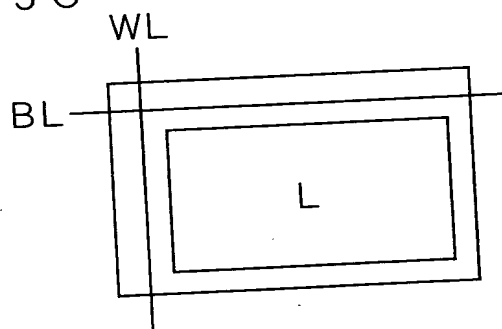
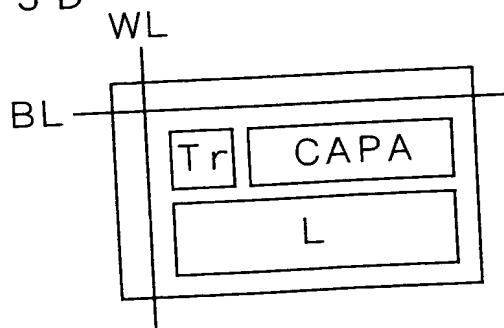


FIG. 5D



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FIG. 6

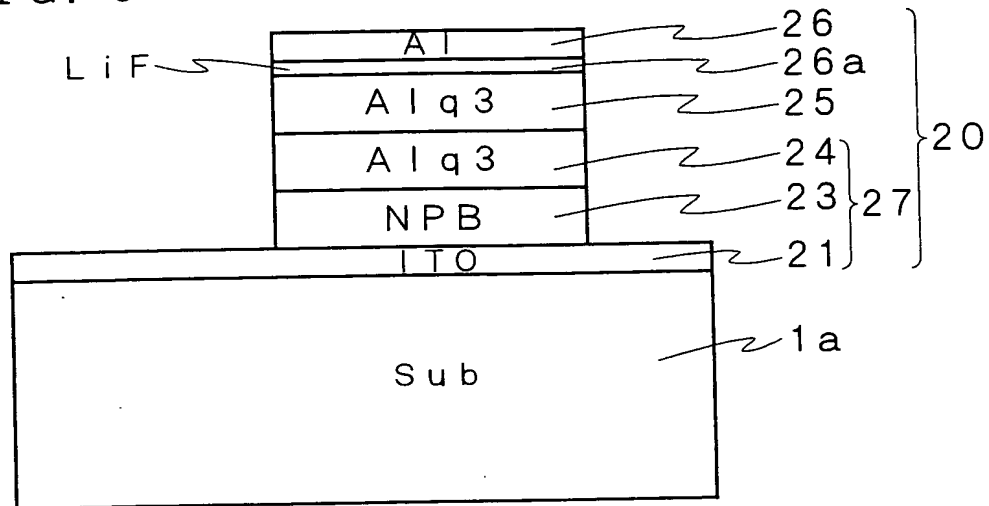
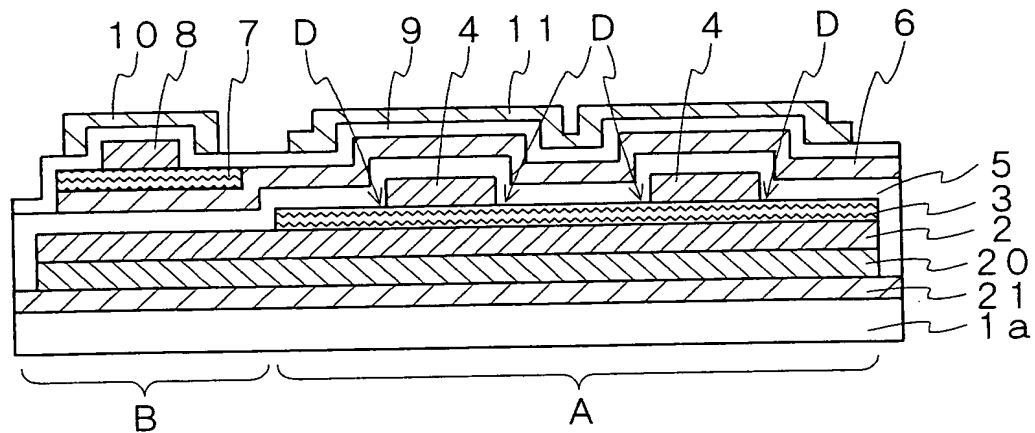


FIG. 7



A cross-sectional view of a semiconductor device. The device consists of a substrate 1a with a base layer 1. Above the base layer is a series of alternating layers 2, 20, and 21. A wavy line indicates an interface between layer 2 and layer 20. Above these layers is a thick layer 3, which is further divided into sub-layers 5 and 6. The top surface of the device is stepped, with the steps defined by layers 4, 9, 10, 11, 12, 13, 14, and 15. Brackets at the bottom indicate two regions: B on the left and A on the right.

A cross-sectional view of a semiconductor device 300. The device consists of a substrate 31 with a patterned layer 32 on top. Layer 32 has two rectangular openings 33 and 34. A layer 35 is deposited over layer 32, filling the openings 33 and 34. A layer 36 is deposited over layer 35, forming a continuous film across the top surface and the openings 33 and 34.